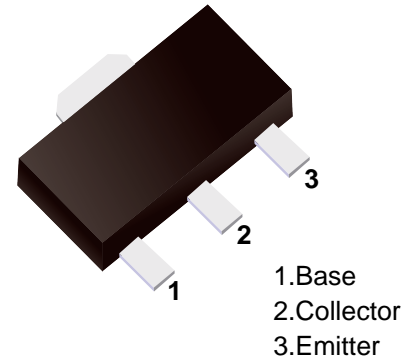


D882

■ NPN Transistors

■ Features

- NPN transistor High current output up to 3A
- Low Saturation Voltage
- Complement to 2SB772



■ Simplified outline(SOT-89)

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CB0}	40	V
Collector to Emitter Voltage	V_{CE0}	30	V
Emitter to Base Voltage	V_{EB0}	6	V
Collector Current to Continuous	I_c	3	A
Collector Dissipation	P_c	0.5	W
Junction Temperature	T_J	150	$^\circ\text{C}$
Storage Temperature	T_{stg}	-55 to 150	$^\circ\text{C}$

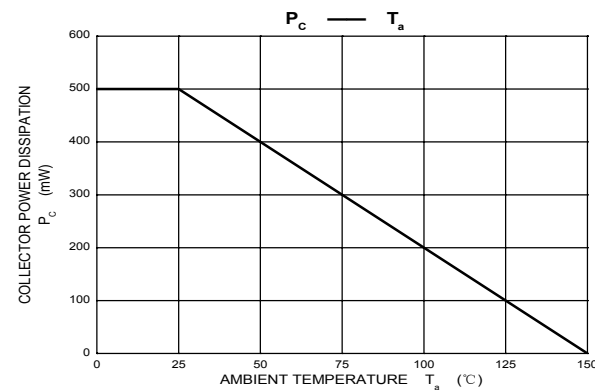
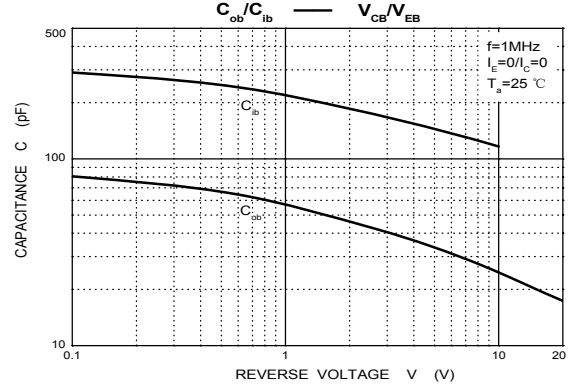
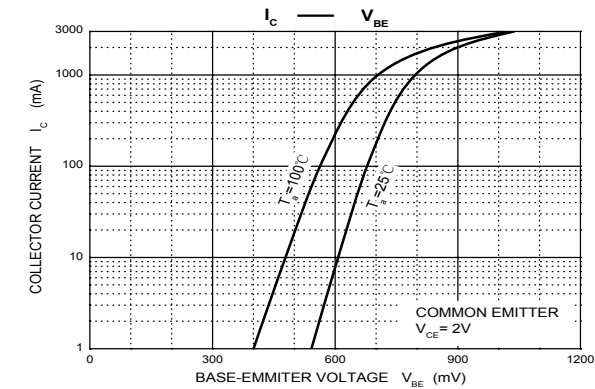
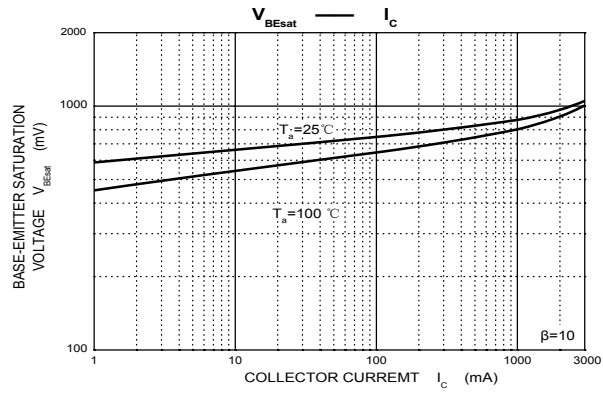
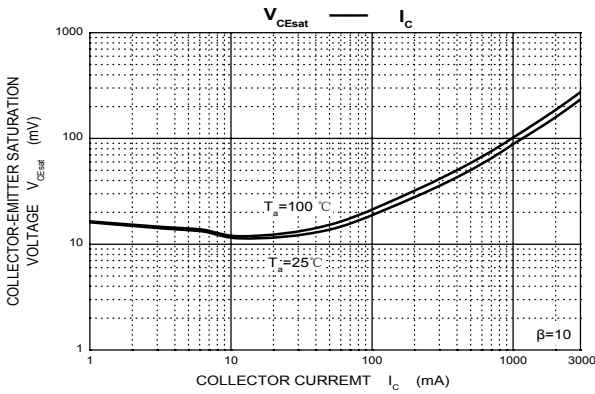
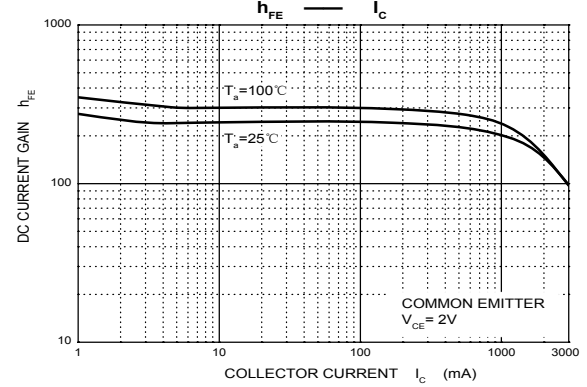
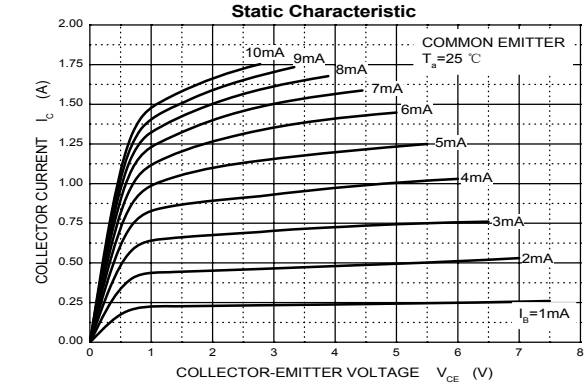
■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Testconditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	V_{CB0}	$I_c=100\mu\text{A}$, $I_E=0$	40			V
Collector-emitter breakdown voltage	V_{CE0}	$I_c=10\text{mA}$, $I_B=0$	30			V
Emitter-base breakdown voltage	V_{EB0}	$I_E=100\mu\text{A}$, $I_c=0$	6			V
Collector cut-off current	I_{CB0}	$V_{CB}=40\text{V}$, $I_E=0$			1	μA
Collector cut-off current	I_{CE0}	$V_{CE}=30\text{V}$, $I_B=0$			10	μA
Emitter cut-off current	I_{EB0}	$V_{EB}=6\text{V}$, $I_c=0$			1	μA
DC current gain	h_{FE}	$V_{CE}=2\text{V}$, $I_c=1\text{A}$	60		400	
		$V_{CE}=2\text{V}$, $I_c=100\text{mA}$	32			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_c=2\text{A}$, $I_B=0.2\text{A}$			0.5	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_c=2\text{A}$, $I_B=0.2\text{A}$			1.5	V
Transition frequency	f_T	$V_{CE}=5\text{V}$, $I_c=0.1\text{mA}$, $f=10\text{MHz}$	50			MHz

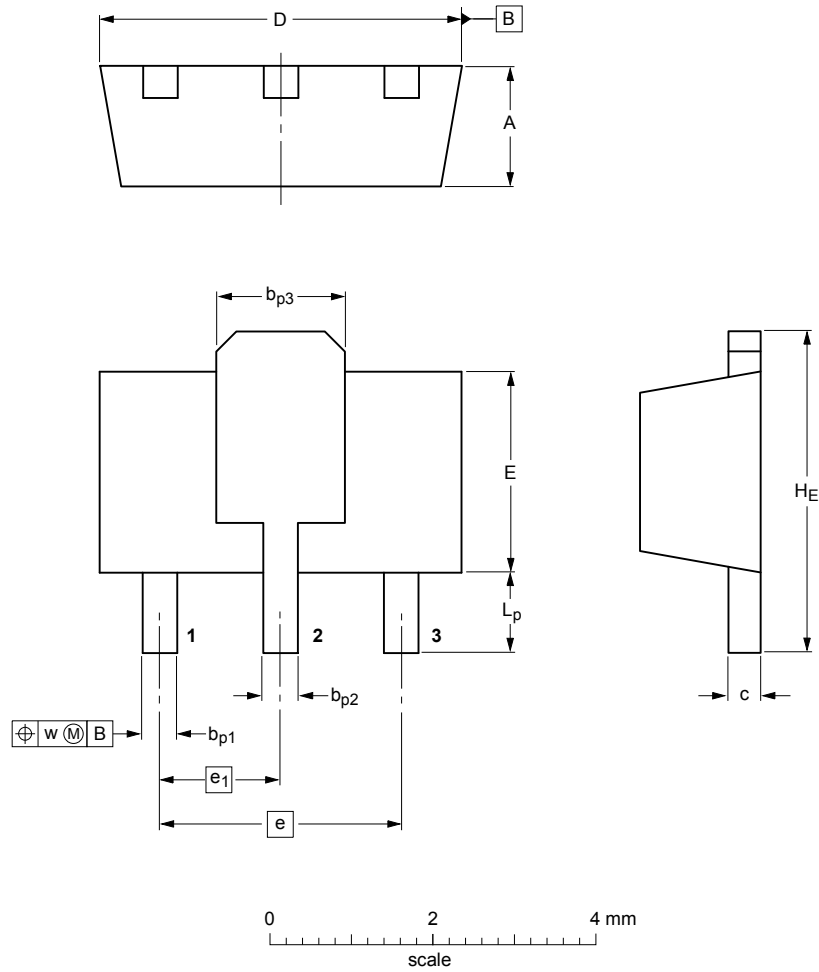
■ Classification of $h_{fe}(1)$

Type	2SD882-R	2SD882-Q	2SD882-P	2SD882-E
Range	60-120	100-200	160-320	200-400

■ Typical Characteristics



■ SOT-89



DIMENSIONS (mm are the original dimensions)

UNIT	A	b_{p1}	b_{p2}	b_{p3}	c	D	E	e	e_1	H_E	L_p	w
mm	1.6	0.48	0.53	1.8	0.44	4.6	2.6	3.0	1.5	4.25	1.2	0.13
	1.4	0.35	0.40	1.4	0.23	4.4	2.4					